

Zexuan Zhang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

11 papers	235 citations	5 h-index	11 g-index
11 ext. papers	293 ext. citations	3 avg, IF	2.8 L-index

#	Paper	IF	Citations
11	Distributed polarization-doped GaN pB diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. <i>Applied Physics Letters</i> , 2022 , 120, 122111	3.4	0
10	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 119, 162104	3.4	6
9	Epitaxial Ferrimagnetic Mn4N Thin Films on GaN by Molecular Beam Epitaxy. <i>IEEE Transactions on Magnetics</i> , 2021 , 1-1	2	0
8	SpinOrbit torque field-effect transistor (SOTFET): Proposal for a magnetoelectric memory. <i>Applied Physics Letters</i> , 2020 , 116, 242405	3.4	4
7	Magnetic properties of MBE grown Mn4N on MgO, SiC, GaN and Al2O3 substrates. <i>AIP Advances</i> , 2020 , 10, 015238	1.5	3
6	The new nitrides: layered, ferroelectric, magnetic, metallic and superconducting nitrides to boost the GaN photonics and electronics eco-system. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC0801	1.4	43
5	Materials Relevant to Realizing a Field-Effect Transistor Based on SpinOrbit Torques. <i>IEEE Journal on Exploratory Solid-State Computational Devices and Circuits</i> , 2019 , 5, 158-165	2.4	1
4	2.44 kV Ga2O3 vertical trench Schottky barrier diodes with very low reverse leakage current 2018 ,		23
3	1230 V EGa2O3 trench Schottky barrier diodes with an ultra-low leakage current of . <i>Applied Physics Letters</i> , 2018 , 113, 202101	3.4	61
2	Breakdown mechanism in 1 kA/cm2 and 960 V E-mode EGa2O3 vertical transistors. <i>Applied Physics Letters</i> , 2018 , 113, 122103	3.4	91
1	Very High Density ($>10^{14} \text{ cm}^{-2}$) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. <i>Advanced Electronic Materials</i> , 2101120	6.4	3